

BT138X series D and E

12 A four-quadrant triacs, sensitive gate
Rev. 03 — 10 March 2008

Product data sheet

Product profile

1.1 General description

Passivated sensitive gate triac in a SOT186A full pack plastic package.

1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs
- Isolated mounting base
- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- High isolation voltage

1.3 Applications

General purpose switching and phase control

230 V lamp dimmers

1.4 Quick reference data

- $V_{DRM} \le 600 \text{ V (BT138X-600D)}$
- $V_{DRM} \le 600 \text{ V (BT138X-600E)}$
- $V_{DRM} \le 800 \text{ V (BT138X-800E)}$
- $I_{GT} \le 5 \text{ mA (BT138X-600D)}$
- $I_{GT} \le 10 \text{ mA (BT138X-600E)}$
- $I_{GT} \le 10 \text{ mA (BT138X-800E)}$
- $I_{T(RMS)} \le 12 A$
- $I_{TSM} \le 95 \text{ A (t = 20 ms)}$
- $I_{GT} \le 10 \text{ mA } (T2-G+) \text{ (BT138X-600D)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138X-600E)}$
- $I_{GT} \le 25 \text{ mA } (T2-G+) \text{ (BT138X-800E)}$



2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------------------|--------------------|----------------|
| 1 | main terminal 1 (T1) | | N 1 |
| 2 | main terminal 2 (T2) | mb | T2—T1 |
| 3 | gate (G) | | `G sym051 |
| mb | mounting base; isolated | | |
| | | SOT186A (TO-220F) | |

3. Ordering information

Table 2. Ordering information

| Type number | Package | | | | | | |
|-------------|---------|---|---------|--|--|--|--|
| | Name | Description | Version | | | | |
| BT138X-600D | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; | SOT186A | | | | |
| BT138X-600E | | 3-lead TO-220 'full pack' | | | | | |
| BT138X-800E | | | | | | | |

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

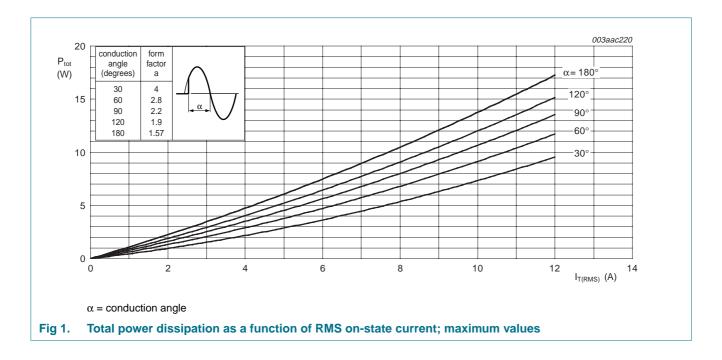
| Parameter | Conditions | Min | Max | Unit |
|--------------------------------------|---|--|-----|--|
| repetitive peak off-state voltage | BT138X-600D | [1] _ | 600 | V |
| | BT138X-600E | [1] _ | 600 | V |
| | BT138X-800E | - | 800 | V |
| RMS on-state current | full sine wave; $T_h \le 56$ °C; see Figure 4 and 5 | - | 12 | Α |
| non-repetitive peak on-state current | full sine wave; $T_j = 25$ °C prior to surge; see Figure 2 and 3 | | | |
| | t = 20 ms | - | 95 | Α |
| | t = 16.7 ms | - | 105 | Α |
| I ² t for fusing | t _p = 10 ms | - | 45 | A ² s |
| rate of rise of on-state current | $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$ | | | |
| | T2+ G+ | - | 50 | A/μs |
| | T2+ G- | - | 50 | A/μs |
| | T2- G- | - | 50 | A/μs |
| | T2- G+ | - | 10 | A/μs |
| | RMS on-state current non-repetitive peak on-state current I ² t for fusing | $BT138X-600E \\ BT138X-800E \\ RMS \ on-state \ current \\ full \ sine \ wave; \ T_h \le 56 \ ^{\circ}C; \\ see \ \underline{Figure} \ 4 \ and \ 5 \\ \hline non-repetitive \ peak \ on-state \ current \\ \hline Example 10 \ ms \\ \hline rate \ of \ rise \ of \ on-state \ current \\ \hline I_{TM} = 20 \ A; \ I_G = 0.2 \ A; \ dI_G/dt = 0.2 \ A/\mu s \\ \hline T2+ \ G- \\ \hline T2- \ G- \\ \hline $ | | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ |

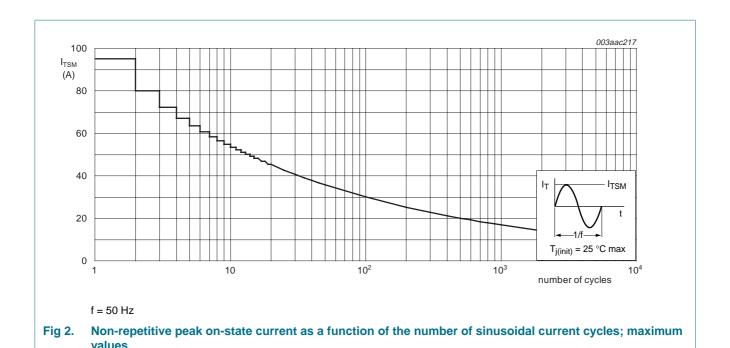
 Table 3.
 Limiting values ...continued

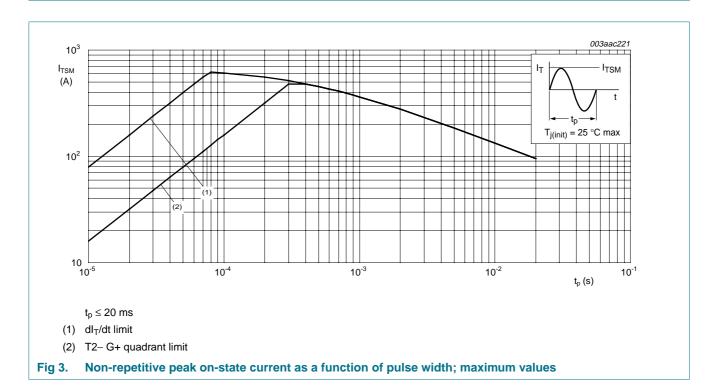
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|-----------------------|-----|------|------|
| I_{GM} | peak gate current | | - | 2 | Α |
| P_GM | peak gate power | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | +150 | °C |
| T _j | junction temperature | | - | 125 | °C |

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.







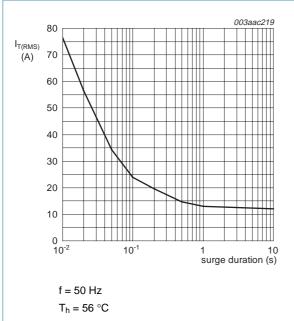


Fig 4. RMS on-state current as a function of surge duration; maximum values

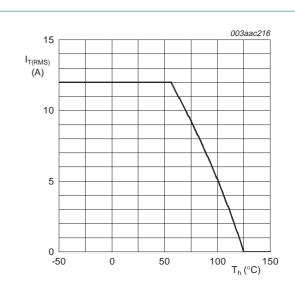
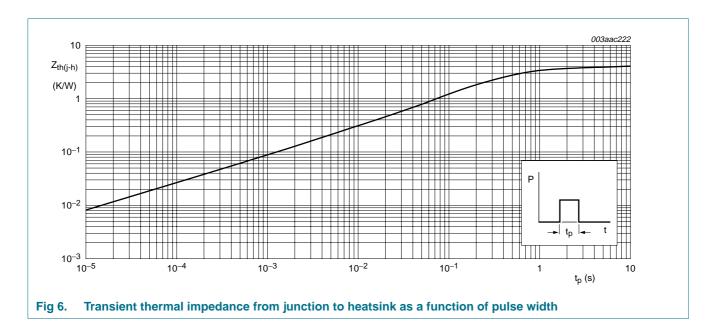


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|--|--------------------------|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle; see Figure 6 | - | - | 4.0 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | full cycle; in free air | - | 55 | - | K/W |



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------------|-----------------------|---|-----|-----|------|------|
| $V_{\text{isol}(\text{RMS})}$ | RMS isolation voltage | from all three terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz ; sinusoidal waveform; relative humidity $\leq 65 \text{ \%}$; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | from pin 2 to external heatsink; f = 1 MHz | - | 10 | - | pF |

7. Static characteristics

Table 6. Static characteristics

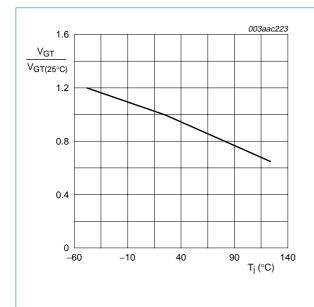
 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

| Symbol Parameter | | Conditions | | BT138X-600D | | BT138X-600E BT138X-800E | | | Unit |
|------------------|----------------------|---|------|-------------|------|----------------------------|-----|------|------|
| | | | Min | Тур | Max | Min | Тур | Max | |
| I_{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 8}}{}$ | • | ' | | | · | ' | |
| | | T2+ G+ | - | 1.3 | 5 | - | 2.5 | 10 | mA |
| | | T2+ G- | - | 2.8 | 5 | - | 4.0 | 10 | mA |
| | | T2- G- | - | 3.2 | 5 | - | 5.0 | 10 | mA |
| | | T2- G+ | - | 5.5 | 10 | - | 11 | 25 | mA |
| IL | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 10}{\text{Figure } 10}$ | | | | | | | |
| | | T2+ G+ | - | - | 15 | - | - | 30 | mA |
| | | T2+ G- | - | - | 20 | - | - | 40 | mA |
| | | T2- G- | - | - | 15 | - | - | 30 | mA |
| | | T2- G+ | - | - | 20 | - | - | 40 | mA |
| I _H | holding current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{\text{Figure } 11}$ | - | - | 10 | - | - | 30 | mA |
| V_{T} | on-state voltage | I _T = 15 A; see <u>Figure 9</u> | - | 1.4 | 1.65 | - | 1.4 | 1.65 | V |
| V_{GT} | gate trigger voltage | $I_T = 0.1 \text{ A; see } \underline{\text{Figure 7}}$ | | | | | | | |
| | | V _D = 12 V | - | 0.7 | 1.5 | - | 0.7 | 1.5 | V |
| | | $V_D = V_{DRM}$; $T_j = 125 ^{\circ}C$ | 0.25 | 0.4 | - | 0.25 | 0.4 | - | V |
| I_D | off-state current | $V_D = V_{DRM(max)}$; $T_j = 125 ^{\circ}C$ | - | 0.1 | 0.5 | - | 0.1 | 0.5 | mA |

8. Dynamic characteristics

Table 7. Dynamic characteristics

| Symbol | Parameter | Conditions | BT13 | BT138X-600D | | BT138X-600E BT138X-800E | | | Unit |
|---------------------|-----------------------------------|---|------|-------------|-----|----------------------------|-----|-----|------|
| | | | Min | Тур | Max | Min | Тур | Max | |
| dV _D /dt | rate of rise of off-state voltage | $V_{DM} = 0.67 \times V_{DRM(max)};$ exponential waveform; gate open circuit; $T_j = 125 ^{\circ}C$ | - | 50 | - | - | 150 | - | V/μs |
| t _{gt} | gate-controlled turn-on time | $I_{TM} = 16 \text{ A};$ $V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$ | - | 2 | - | - | 2 | - | μs |



1 003aac224

1GT (25°C)

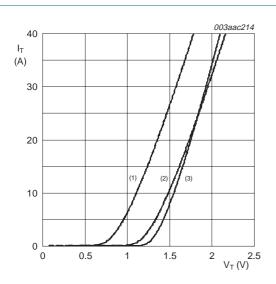
2 (3)
(4)
(4)
(1)
(2)
(3)
(4)
(4)
(4)
(7)
(°C)

- (1) T2-G+
- (2) T2-G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature

Fig 8. Normalized gate trigger current as a function of junction temperature

BT138X_SER_D_E_3



 $V_0 = 1.175 \text{ V}$

 $R_s = 0.032 \Omega$

(1) $T_j = 125 \,^{\circ}C$; typical values

(2) T_i = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig 9. On-state current as a function of on-state voltage

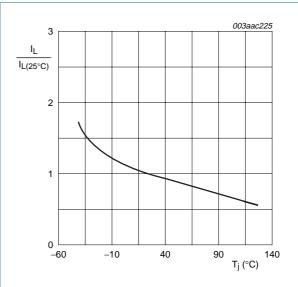


Fig 10. Normalized latching current as a function of junction temperature

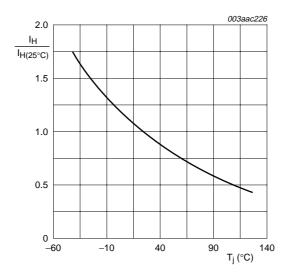
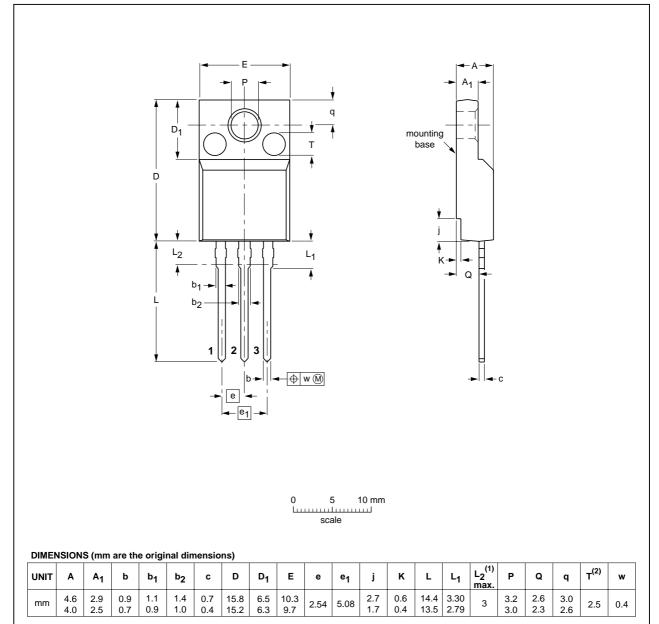


Fig 11. Normalized holding current as a function of junction temperature

9. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------------|----------|------------|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | 1330E DATE |
| SOT186A | | 3-lead TO-220F | | | | -02-04-09 06-02-14 |

Fig 12. Package outline SOT186A (TO-220F)

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

10. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------|-----------------------------------|--|------------------------|-----------------------|
| BT138X_SER_D_E_3 | 20080310 | Product data sheet | - | BT138X_SERIES_E_2 |
| Modifications: | | of this data sheet has been of NXP Semiconductors. | redesigned to comply v | vith the new identity |
| | Legal texts I | have been adapted to the ne | ew company name whe | ere appropriate. |
| | • BT138X-600 | OD product added. | | |
| | Table 7 "Dyr | namic characteristics": dV _D / | dt uprated for BT138X | series E. |
| BT138X_SERIES_E_2 | 20010601 | Product data sheet | - | BT138X_SERIES_E_1 |
| BT138X_SERIES_E_1 | 19970901 | Product data sheet | - | - |
| | | | | |

BT138X series D and E

12 A four-quadrant triacs, sensitive gate

11. Legal information

11.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BT138X series D and E

12 A four-quadrant triacs, sensitive gate

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